NTR1P02LT1

Power MOSFET

−20 V, −1.3 A, P−Channel SOT−23 Package

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are dc−dc converters and power management in portable and battery−powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOT−23 Surface Mount Package Saves Board Space
- Pb−Free Package is Available

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	−20	V
Gate−to−Source Voltage − Continuous	V_{GS}	±12	V
Drain Current − Continuous @ T_A = 25°C − Pulsed Drain Current ($t_p \le 10$ μs)	I_D I_{DM}	−1.3 −4.0	A A
Total Power Dissipation @ T_A = 25°C	P_D	400	mW
Operating and Storage Temperature Range	T_J, T_{stg}	− 55 to 150	°C
Thermal Resistance − Junction−to−Ambient	$R_{\theta JA}$	300	°C/W
Maximum Lead Temperature for Soldering Purposes, (1/8″ from case for 10 s)	T_L	260	°C

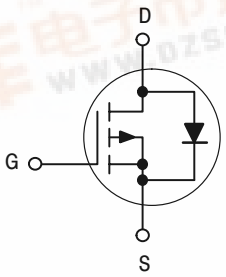
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

ON Semiconductor®

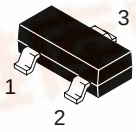
http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
−20 V	220 mΩ	−1.3 A

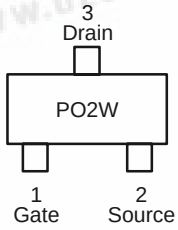
P−Channel



MARKING DIAGRAM/ PIN ASSIGNMENT



SOT−23
CASE 318
STYLE 21



PO2 = Specific Device Code
W = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NTR1P02LT1	SOT−23	3000 Tape & Reel
NTR1P02LT1G	SOT−23 (Pb−Free)	3000 Tape & Reel
NTR1P02LT3	SOT−23	10,000 Tape & Reel
NTR1P02LT3G	SOT−23 (Pb−Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage (V_{GS} = 0 V, I_D = −10 μA)		$V_{(BR)DSS}$	−20			V
Zero Gate Voltage Drain Current (V_{DS} = −16 V, V_{GS} = 0 V) (V_{DS} = −16 V, V_{GS} = 0 V, T_J = 125°C)		I_{DSS}			−1.0 −10	μA
Gate−Body Leakage Current (V_{GS} = ± 12 V, V_{DS} = 0 V)		I_{GSS}			±100	nA
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = −250 μA)		$V_{GS(th)}$	−0.7	−1.0	−1.25	V
Static Drain−to−Source On−Resistance (V_{GS} = −4.5 V, I_D = −0.75 A) (V_{GS} = −2.5 V, I_D = −0.5 A)		$r_{DS(on)}$		0.135 0.190	0.22 0.35	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = −5.0 V)	C_{iss}		225		pF
Output Capacitance	(V_{DS} = −5.0 V)	C_{oss}		130		
Transfer Capacitance	(V_{DG} = −5.0 V)	C_{rss}		55		
SWITCHING CHARACTERISTICS (Note 2)						
Turn−On Delay Time	(V_{DD} = −5.0 V, I_D = −1.0 A, R_L = 5.0 Ω, R_G = 6.0 Ω)	$t_{d(on)}$		7.0		ns
Rise Time		t_r		15		
Turn−Off Delay Time		$t_{d(off)}$		18		
Fall Time		t_f		20		
Total Gate Charge	(V_{DS} = −16 V, I_D = −1.5 A, V_{GS} = −4.0 V)	Q_T		5500		pC
SOURCE−DRAIN DIODE CHARACTERISTICS						
Continuous Current		I_S			−0.6	A
Pulsed Current		I_{SM}			−0.75	
Forward Voltage (Note 2) (V_{GS} = 0 V, I_S = −0.6 A)		V_{SD}			−1.0	V
Reverse Recovery Time	(I_S = −1.0 A, V_{GS} = 0 V, dI_S/dt = 100 A/μs)	t_{rr}		16		ns
		t_a		11		
		t_b		5.5		
Reverse Recovery Stored Charge		Q_{RR}		0.0085		μC

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

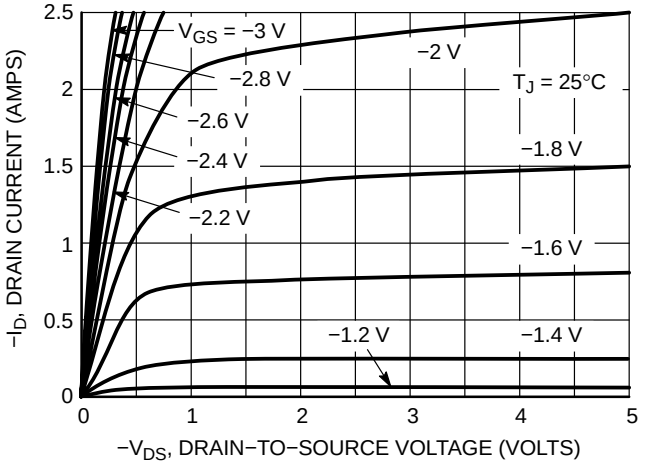


Figure 1. On−Region Characteristics

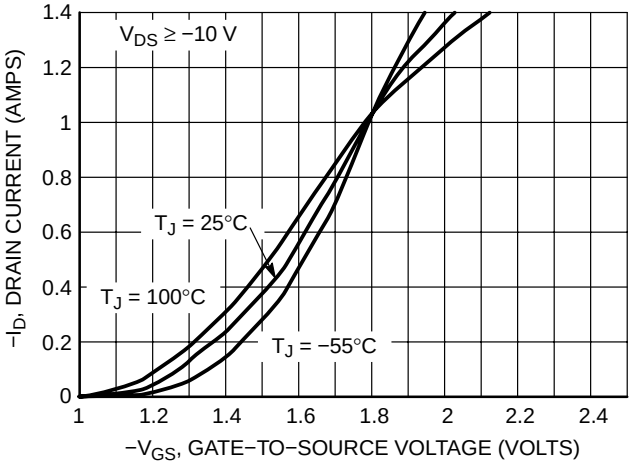


Figure 2. Transfer Characteristics

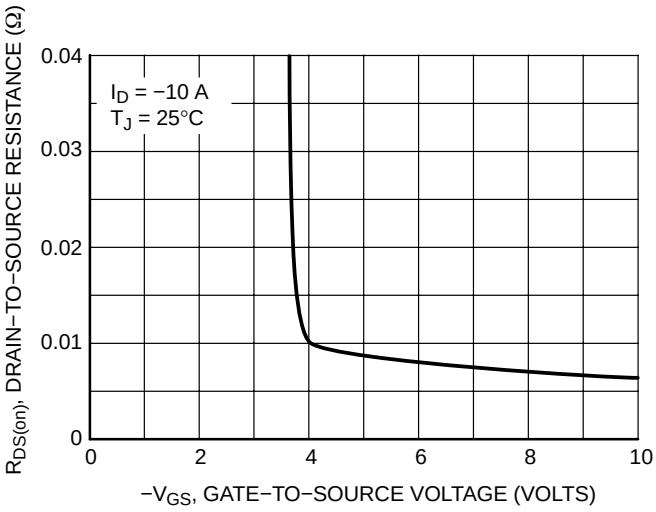


Figure 3. On−Resistance versus Gate−to−Source Voltage

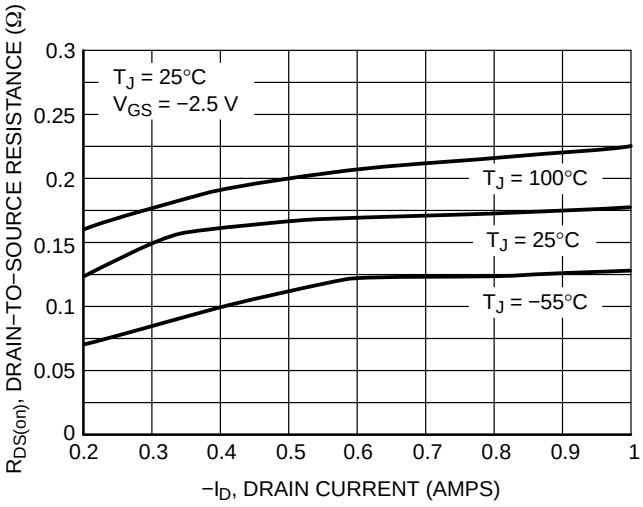


Figure 4. On−Resistance versus Drain Current and Gate Voltage

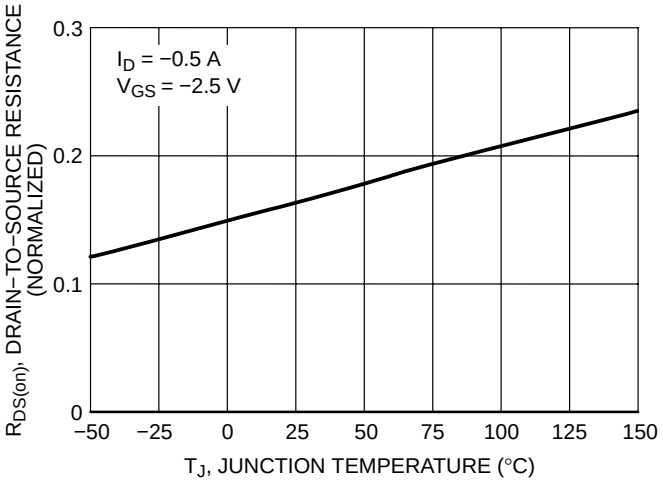


Figure 5. On−Resistance Variation with Temperature

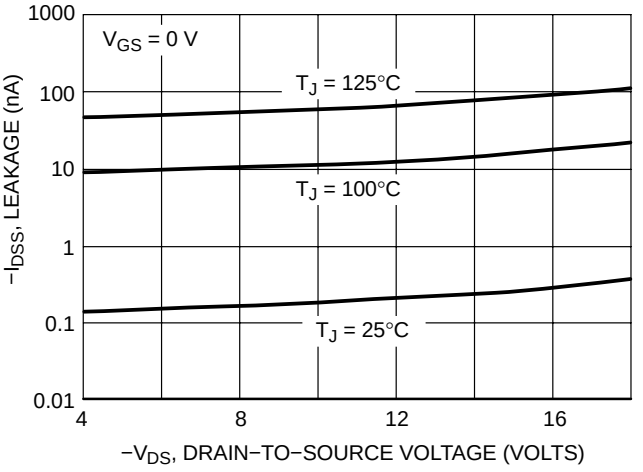


Figure 6. Drain−to−Source Leakage Current versus Voltage

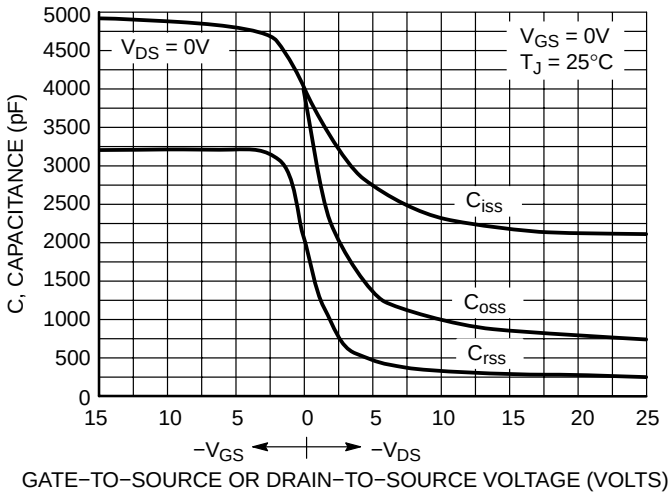


Figure 7. Capacitance Variation

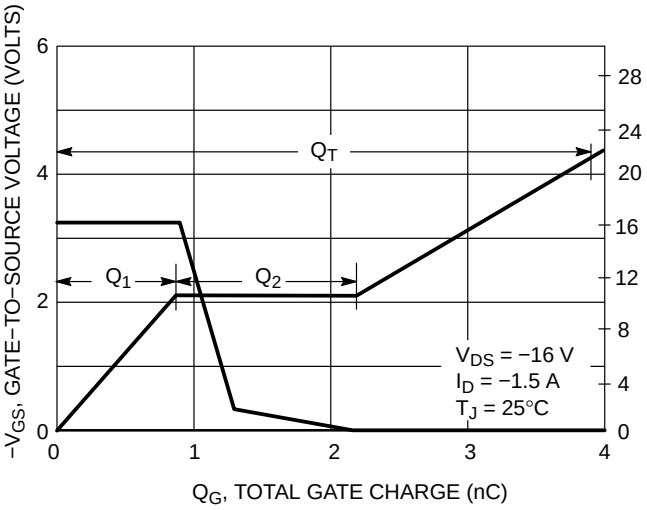


Figure 8. Gate−to−Source and Drain−to−Source Voltage versus Total Charge

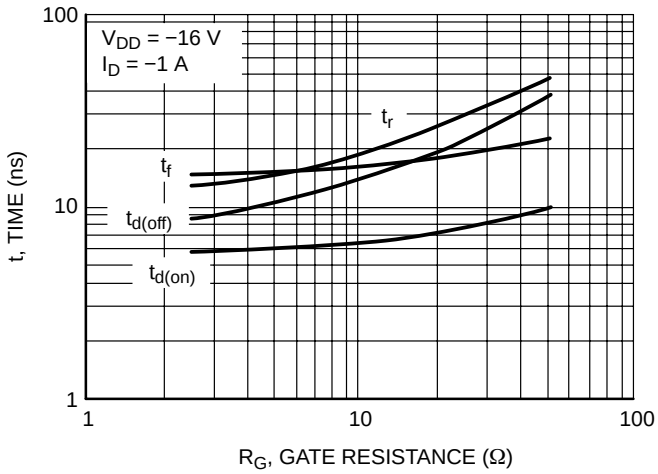


Figure 9. Resistive Switching Time Variation versus Gate Resistance

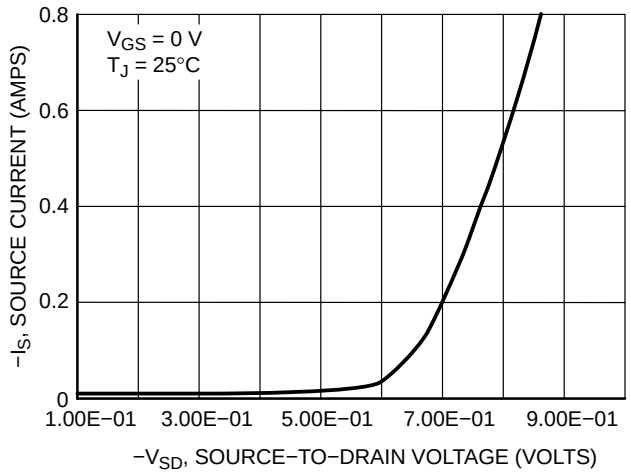
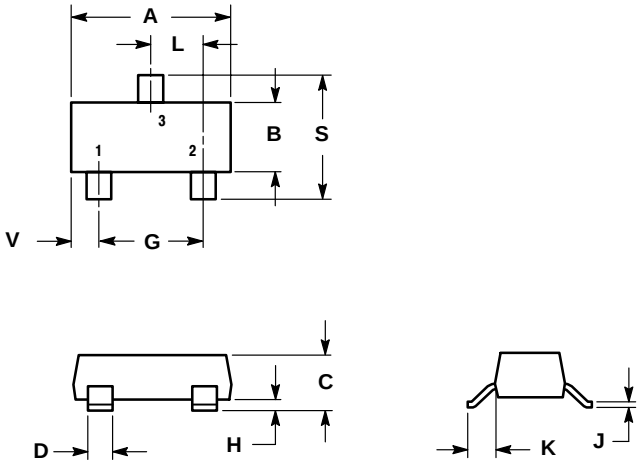


Figure 10. Diode Forward Voltage versus Current

NTR1P02LT1

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−09
ISSUE AJ

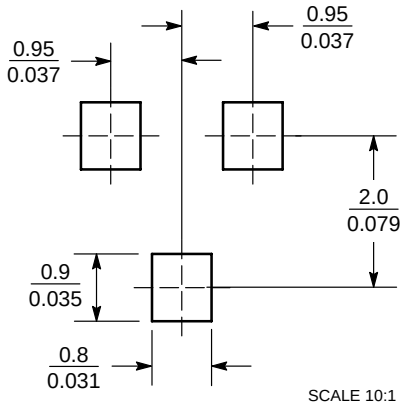


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIUMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01, −02, AND −06 OBSOLETE, NEW STANDARD 318−09.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
H	0.0040	0.0098	0.10	0.25
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.